

SCHEELITE RELATED COMPOUNDS AS EFFICIENT PHOSPHOR FOR PC-WLEDs AND THERMOGRAPHIC APPLICATION

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Scheelite (CaWO_4) related compounds $(\text{A}', \text{A}'')_n[(\text{B}', \text{B}'')\text{O}_4]_m$ with $\text{B}', \text{B}'' = \text{W}$ and/or Mo are promising new materials for red phosphors in pc-WLEDs (phosphor-converted white-light-emitting-diode) and solid-state lasers. Scheelites can be prepared with a large concentration of vacancies in the A sublattice, giving compositions characterized by a $(\text{A}' + \text{A}''):(\text{B}'\text{O}_4 + \text{B}''\text{O}_4)$ ratio different from 1:1. The creation of cation vacancies in the scheelite-type framework and the ordering of A cations and vacancies are a new factor in controlling the scheelite-type structure and properties. The creation and ordering of A-cation vacancies and the effect of cation substitutions in the scheelite-type framework are investigated as a factor controlling the scheelite-type structure and luminescent properties of $\text{Ag}_x \text{R}^{3+}_{(2-x)/3} \square_{(1-2x)/3} \text{WO}_4$ ($\text{R} = \text{Eu}, \text{Sm}$) and $\text{Ag}_x \text{Gd}_{(2-x)/3-0.3} \text{Eu}_{0.3} \square_{(1-2x)/3} \text{WO}_4$ scheelite-type phases. Transmission electron microscopy also confirmed the (3+1)D incommensurately modulated character of $\text{Ag}_x \text{R}^{3+}_{(2-x)/3} \square_{(1-2x)/3} \text{WO}_4$ ($\text{R} = \text{Eu}, \text{Sm}; x = 0.286, 0.2$) phases.

The luminescent properties of all phases under near-ultraviolet (n-UV) light have been investigated were related to the structural properties of the materials. Eu-based phosphors emit intense red light dominated by the ${}^5\text{D}_0 - {}^7\text{F}_2$ transition at 613 nm, along with other transitions from the ${}^5\text{D}_0$ excited states. The excitation spectra of $\text{Ag}_x \text{Eu}^{3+}_{(2-x)/3} \text{WO}_4$ ($x = 0.5, 0.286, 0.2$) phosphors show the strongest absorption at 395 nm, which matches well with the commercially available n-UV-emitting GaN-based LED chip. The intensity of the ${}^5\text{D}_0 \rightarrow {}^7\text{F}_2$ transition on the $\text{Ag}_x \text{Eu}^{3+}_{(2-x)/3} \text{WO}_4$ emission spectra is reduced almost 7 times with decreasing x from 0.5 to 0 but it does not change practically in the range from $x = 0.286$ to $x = 0.200$. The emission spectra of Gd-containing samples show a completely different trend as compared to only Eu-containing samples. The Eu^{3+} emission under excitation of Eu^{3+} (${}^5\text{L}_6$) level ($\lambda_{\text{ex}} = 395$ nm) increases more than 2.5 times with the increasing Gd^{3+} content from 0.2 ($x = 0.5$) to 0.3 ($x = 0.2$) in the $\text{Ag}_x \text{Gd}_{(2-x)/3-0.3} \text{Eu}_{0.3} \text{WO}_4$. Sm-based phosphors under n-UV light show the characteristic emission lines in the range of 550–720 nm, corresponding to ${}^4\text{G}_{5/2} \rightarrow {}^6\text{H}_J$ ($J = 5/2, 7/2, 9/2$ and $11/2$) transitions of Sm^{3+} ions, with the $J = 9/2$ transition at the ~648 nm region being dominant for all PL spectra. Different temperature dependencies were found for the intensity of the ${}^4\text{G}_{5/2} \rightarrow {}^6\text{H}_{9/2}$ and ${}^4\text{G}_{5/2} \rightarrow {}^6\text{H}_{7/2}$ bands. The emission intensity ratios (R) for these bands vary reproducibly with temperature, allowing the use of these materials as thermographic phosphors.

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